

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	15093	((257/79) or (257/88) or (257/93) or (257/98) or (257/99) or (257/499) or (257/501) or (257/678) or (257/905) or (257/906) or (257/911)).OCL.S.	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/06/19 14:25
L2	3	1 and integrated adj circuit and (silicon Si) near1 substrate and (planari?e planari?ing planari?ation) and thin adj film and metal adj (film layer) near4 (planar flat) and inorganic	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/19 14:28
L3	0	1 and (IC integrated adj circuit).clm. and (silicon Si) near1 substrate.clm. and (planari?e planari?ing planari?ation).clm. and thin adj film.clm. and metal adj (film layer) near4 (planar flat).clm. and inorganic.clm.	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/19 14:29
L4	0	(oki adj data.as. ogihara.in. sakuta.in. abiko.in. fujiwara.in.) and (IC integrated adj circuit).clm. and (silicon Si) near1 substrate.clm. and (planari?e planari?ing planari?ation).clm. and thin adj film.clm. and metal adj (film layer) near4 (planar flat).clm. and inorganic.clm.	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/19 14:32
S1	4	"743104".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 13:38

S2	1	(US-20040135157-\$).did.	US-PGPUB	OR	OFF	2005/05/24 11:53
S3	0	jp-60206889\$-\$\$.did.	US-PGPUB	OR	OFF	2005/05/24 11:54
S4	1	jp-60206889\$-\$\$.did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 11:58
S5	2	jp-10063807\$-\$\$.did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 11:58
S6	152	(257/93).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/06/11 19:50
S7	209	(257/501).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/06/11 19:50
S8	360	S6 S7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 19:51
S9	127	S8 and (light adj emitting light-emitting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 19:51
S10	1	S8 and (light adj emitting light-emitting) and (("without" "no") adj wire adj bond\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 19:54

S11	127	S8 and (light adj emitting light-emitting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 19:54
S12	34	S8 and (light adj emitting light-emitting) and planar \$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 19:54
S13	14	(US-6773943-\$ or US-6692845-\$ or US-6472718-\$ or US-6403985-\$ or US-6339233-\$ or US-6114715-\$ or US-5955747-\$ or US-5866922-\$ or US- 5663581-\$ or US-5115284-\$ or US-4984035-\$ or US-4956683-\$ or US-4335501-\$ or US-T979005-\$). did.	USPAT	OR	OFF	2005/06/11 20:11
S14	4	S13 and print\$3	US-PGPUB; USPAT	OR	OFF	2005/06/11 20:33
S15	5349	((257/79) or (257/88) or (257/93) or (257/99) or (257/499) or (257/501) or (257/678) or (257/687)). CCLS.	US-PGPUB; USPAT	OR	OFF	2005/06/12 20:40
S16	1	S15 and monolithic and substrate near6 integrated adj circuit and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 20:39
S17	2	S15 and substrate near6 integrated adj circuit and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 20:43

S18	0	S15 and monolithic and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 20:43
S19	3	S15 and monolithic and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 20:45
S20	3	S15 and integrated adj circuit near6 substrate and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 20:46
S21	2	S15 and integrated adj circuit near6 (semiconductor silicon) near4 substrate and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 20:47
S22	2	S15 and (IC integrated adj circuit) near6 (semiconductor silicon) near4 substrate and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 20:48
S23	17	(IC integrated adj circuit) near6 (semiconductor silicon) near4 substrate and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 20:55
S24	154	(IC integrated adj circuit) near6 (semiconductor silicon) near4 substrate and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) and thin adj2 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 21:04

S25	2	("5055907").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 21:26
S26	2	("4755866").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 21:30
S27	6922	(light-emitting light adj emitting LED laser diode) adj array and (integrated adj circuit\$2 IC monolithic \$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 21:31
S28	378	(light-emitting light adj emitting LED laser diode) adj array and (integrated adj circuit\$2 IC monolithic \$4) and planariz\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 21:38
S29	189	(light-emitting light adj emitting LED laser adj diode) adj array and (integrated adj circuit\$2 IC monolithic\$4) and planariz\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:22
S30	249	semi-insulating adj substrate.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:23
S31	249	semi-insulating adj substrate.ti. and semi-insulating	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:27

S32	3	semi-insulating adj substrate.ti. and semi-insulating near6 defined	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:33
S33	0	(silicon semiconductor semi-insulating) adj substrate near4 "having" near4 (driver integrated)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:35
S34	0	(silicon semiconductor semi-insulating) adj substrate near4 "wherein" near4 (driver integrated)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:35
S35	0	(silicon semiconductor semi-insulating) adj substrate near10 "wherein" near4 (driver integrated IC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:36
S36	0	(silicon semiconductor semi-insulating) adj substrate near10 "wherein" near10 (driver integrated IC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:36
S37	1481	(silicon semiconductor semi-insulating) adj substrate near10 ("in which" "wherein" "having" "within") near10 (driver integrated IC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:36
S38	72	(silicon semiconductor semi-insulating) adj substrate near10 ("in which" "wherein" "having" "within") near10 (driver integrated IC) and planariz \$5 and (LED light-emitting light adj emitting laser adj diode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:51

S39	4756	(silicon semiconductor) adj substrate and thin adj2 film and passivation and (integrated adj circuit IC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:52
S40	3231	(silicon semiconductor) adj substrate and thin adj2 film and passivation and (integrated adj circuit IC) and "257"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:53
S41	444	(silicon semiconductor) adj substrate and thin adj2 film and passivation adj (layer film) near6 substrate and (integrated adj circuit IC) and "257"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:56
S42	317	(silicon semiconductor) adj substrate and thin adj2 film and passivation adj (layer film) near6 substrate and (integrated adj circuit IC) and "257"/\$7.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 00:02
S43	54	(silicon semiconductor) adj substrate and thin adj2 film and planariz\$5 adj (layer film) near6 substrate and (integrated adj circuit IC) and "257"/\$7.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 00:02
S44	2	"5492851".pn. and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 15:03
S45	2	"4902637".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 16:20

S46	0	(integrated adj circuit adj layer 1C adj layer) and (planarization planarize) and (light-emitting light adj emitting diode) adj array	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 15:11
S47	0	(integrated adj circuit adj layer 1C adj layer) and (planarization planarize) and (thin adj 2 film light-emitting light adj emitting diode) adj array	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 15:12
S48	79	(integrated adj circuit adj layer 1C adj layer) and (planarization planarize) and (thin adj 2 film light-emitting light adj emitting diode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 15:22
S49	15	(US-20050087817-\$ or US-20040155302-\$ or US-20040155301-\$ or US-20040016976-\$ or US-20040012053-\$ or US-20040007746-\$ or US-20030067043-\$).did. or (US-6903427-\$ or US-6861715-\$ or US-6812488-\$ or US-6717222-\$ or US-6706546-\$ or US-6690845-\$ or US-6684007-\$ or US-6611635-\$).did.	US-PGPUB; USPAT	OR	OFF	2005/06/12 15:22
S50	4	S49 and thin adj film near 5 planarize\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 15:57
S51	0	S49 and thin adj film near 5 planarize\$5 and integrated adj circuit adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 15:25

S52	4	S49 and thin adj film near5 planariz\$5 and (IC adj layer integrated adj circuit adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 15:28
S53	4	S49 and thin adj film near5 planariz\$5 and (IC adj layer integrated adj circuit adj layer) and thin adj film adj device	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 15:45
S54	4	S49 and thin adj film near5 planariz\$5 and (IC adj layer integrated adj circuit adj layer) and thin adj film adj device and IC adj chip adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 15:50
S55	0	S49 and thin adj film near5 planariz\$5 and (IC adj layer integrated adj circuit adj layer) and thin adj film adj device and IC adj chip adj layer and vcsel adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 15:51
S56	4	S49 and thin adj film near5 planariz\$5 and (IC adj layer integrated adj circuit adj layer) and thin adj film adj device and IC adj chip adj layer and device adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 15:52
S57	4	S49 and thin adj film near5 planariz\$5 and (IC adj layer integrated adj circuit adj layer) and thin adj film adj device and IC adj chip adj layer and device adj layer and (planari?e planari?ation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 15:53
S58	15	S49 and planariz\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 15:58

S59	0	S49 and planariz\$5 and integrated adj circuit adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 15:58
S60	15	S49 and planariz\$5 and (IC integrated adj circuit) adj2 layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 15:58
S61	15	S49 and planariz\$5 and (IC integrated adj circuit) adj2 layer and thin adj film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 16:00
S62	4	S49 and planariz\$5 and (IC integrated adj circuit) adj2 layer and thin adj film and (light-emitting light adj emitting vcsel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 16:00
S63	4	S49 and planariz\$5 and (IC integrated adj circuit) adj2 layer and thin adj film and (light-emitting light adj emitting vcsel piezoelectric hall)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 16:01
S64	4	S49 and planariz\$5 and (IC integrated adj circuit) adj2 layer and thin adj film and (light-emitting light adj emitting vcsel piezoelectric hall laser adj diode photodetect\$3 photodiode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 16:01
S65	15	IC adj layer near6 stack\$3 and (planari?ation planari?e) and (EO LED light-emitting light adj emitting laser diode vcsel photodiode photodetect \$3 hall adj sensor piezo-electric piezoelectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 17:24

S66	29	cd-rom near4 diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 18:37
S67	5991	memory adj device and memory adj cell adj array and ((semiconductor silicon) adj substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 17:25
S68	2403	memory adj device and memory adj cell adj array.ti, ab,clm. and ((semiconductor silicon) adj substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 17:25
S69	1206	memory adj device and memory adj cell adj array.ti, ab,clm. and ((semiconductor silicon) adj substrate). ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 17:25
S70	687	memory adj device and memory adj cell adj array.ti, ab,clm. and ((semiconductor silicon) adj substrate). ti,ab,clm.	USPAT	OR	ON	2005/06/12 17:26
S71	0	memory adj device and memory adj cell adj array.ti, ab,clm. and ((GaAs) adj substrate).ti,ab,clm.	USPAT	OR	ON	2005/06/12 17:26
S72	0	memory adj device and memory adj cell adj array.ti, ab,clm. and ((GaAs) adj substrate).ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/12 17:26
S73	0	memory adj device and memory adj cell adj array.ti, ab,clm. and ((GaAs AlGaAs) adj substrate).ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/12 17:27

S74	0	memory adj device and memory adj cell adj array.ti, ab,clm. and (SiGe SiC GaAs AlGaAs) adj substrate.ti, ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/12 17:27
S75	0	memory adj device and memory adj cell adj array and (SiGe SiC GaAs AlGaAs) adj substrate.ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/12 17:27
S76	45	memory adj device and (SiGe SiC GaAs AlGaAs) adj substrate.ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/12 17:33
S77	5	memory adj device and (SiC) adj substrate.ti,ab, clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/12 17:34
S78	39	memory adj device and (GaAs) adj substrate.ti,ab, clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/12 17:34
S79	12	config-dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 20:01
S80	8	source near6 common adj ground and memory adj array.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 20:11
S81	31389	CD-ROM and Dvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 20:12

S82	2	CD-ROM and Dvd and memory adj array and laser adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 20:13
S83	2	"5696714".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 20:13
S84	5611	((257/79) or (257/88) or (257/93) or (257/99) or (257/499) or (257/501) or (257/678) or (257/687) or (257/905) or (257/906) or (257/911)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/06/12 20:40
S85	0	S84 and (planari?ation planari?e) and (Si silicon semiconductor) adj thin adj film and (integrated adj circuit IC) adj2 (layer) and (light-emitting light adj emitting laser adj diode photodiode photodetect\$3 hall adj sensor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 20:42
S86	4649	integrated adj circuit and (semiconductor silicon gallium adj arsenide gallium adj nitride gaas gan si) near2 substrate and (planarise planarising planarisation planarize planarization planarizing) and thin adj film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 15:59
S87	806	integrated adj circuit and (semiconductor silicon gallium adj arsenide gallium adj nitride gaas gan si) near2 substrate and (planarise planarising planarisation planarize planarization planarizing) near4 (thin adj film film) and (planarise planarising planarisation planarize planarization planarizing) near4 (layer inter-layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 16:01

S88	6	integrated adj circuit and (semiconductor silicon gallium adj arsenide gallium adj nitride gaas gan si) near2 substrate and (planarise planarising planarisation planarize planarization planarizing) near4 (thin adj film film) and (planarise planarising planarisation planarize planarization planarizing) near4 (layer inter-layer) and electrode and oled	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 16:03
S89	2	integrated adj circuit and (semiconductor silicon gallium adj arsenide gallium adj nitride gaas gan si) near2 substrate and (planarise planarising planarisation planarize planarization planarizing) near4 (thin adj film film) and (planarise planarising planarisation planarize planarization planarizing) near4 (layer inter-layer) and electrode and oled and @ad<"20021225"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 16:04
S90	0	integrated adj circuit and (semiconductor silicon gallium adj arsenide gallium adj nitride gaas gan si) near2 substrate and (planarise planarising planarisation planarize planarization planarizing) near4 (thin adj film film) and (planarise planarising planarisation planarize planarization planarizing) near4 (layer inter-layer) and electrode and (electroluminescent adj layer) and @ad<"20021225"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 16:05
S91	0	integrated adj circuit and (semiconductor silicon gallium adj arsenide gallium adj nitride gaas gan si) near2 substrate and (planarise planarising planarisation planarize planarization planarizing) near4 (thin adj film film) and (planarise planarising planarisation planarize planarization planarizing) near4 (layer inter-layer) and electrode and (electroluminescent adj layer) and @ad<"20021225"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 16:05

S92	9	integrated adj circuit and (semiconductor silicon gallium adj arsenide gallium adj nitride gaas gan si) near2 substrate and (planarise planarising planarisation planarize planarization planarizing) near4 (thin adj film film) and (planarise planarising planarisation planarize planarization planarizing) near4 (layer inter-layer) and electrode and light-emitting and @ad< "20021225"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 16:06
S93	12	integrated adj circuit and (semiconductor silicon gallium adj arsenide gallium adj nitride gaas gan si) near2 substrate and (planarise planarising planarisation planarize planarization planarizing) near4 (thin adj film film) and (planarise planarising planarisation planarize planarization planarizing) near4 (layer inter-layer) and electrode and (light adj emitting light-emitting) and @ad< "20021225"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 16:06
S94	1614	(planari?e planari?ed palanari?ation planari?ing) near2 (region layer) and (planari?e planari?ed palanari?ation planari?ing) near2 (film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:07
S95	1097	(planari?e planari?ed palanari?ation planari?ing) near2 (region layer) and (planari?e planari?ed palanari?ation planari?ing) near2 (film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arseinde gallium adj nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:08
S96	1098	(planari?e planari?ed palanari?ation planari?ing) near2 (region layer) and (planari?e planari?ed palanari?ation planari?ing) near2 (film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:08

S97	534	(planari?e planari?ed palanari?ation planari?ing) near2 (region layer) and (planari?e planari?ed palanari?ation planari?ing) near2 (film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:09
S98	287	(planari?e planari?ed palanari?ation planari?ing) near2 (region layer) and (planari?e planari?ed palanari?ation planari?ing) near2 (film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:10
S99	196	(planari?e planari?ed palanari?ation planari?ing) near2 (region layer) and (planari?e planari?ed palanari?ation planari?ing) near2 (film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:10
S100	15	(planari?e planari?ed palanari?ation planari?ing) near2 (region layer) and (planari?e planari?ed palanari?ation planari?ing) near2 (film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225" and (light-emitting light adj emitting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:13
S101	22	(planari?e planari?ed palanari?ation planari?ing) near2 (region layer) and (planari?e planari?ed palanari?ation planari?ing) near2 (film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225" and (light-emitting light adj emitting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:16

S102	32	(planari?e planari?ed planari?ation planari?ing planar) near2 (region layer) and (planari?e planari?ed planari?ation planari?ing planar) near2 (film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225" and (light-emitting light adj emitting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:37
S103	13	(first second) near1 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225" and (light-emitting light adj emitting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:41
S104	210	(first second) near1 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:45
S105	62	first near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and second near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:47

S106	2	first near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and second near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225" and (light-emitting light adj emitting) and thin adj film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:48
S107	2	first near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and second near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225" and (light-emitting light adj emitting) and (tft thin adj film oft)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:50
S108	2	first near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and second near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225" and (light-emitting light adj emitting) and (tft thin adj film oft silicon-on-insulator "soi")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:51
S109	14	first near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and second near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and (integrated adj circuit IC) and thin adj film and @ad<"20021225" and (light-emitting light adj emitting) and (tft thin adj film oft silicon-on-insulator "soi")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 18:31

S110	2	("20030067043").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/23 18:33
S111	19	"5492851"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/23 18:34
S112	2	("5492851").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/23 18:34
S113	2	S112	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/23 18:42
S114	2	("20050199924").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/23 19:02
S115	2	("20050052823").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/23 19:13
S116	509	(257/752).COLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/23 19:38

S117	22	S116 and (thin adj film adj transistor tft offt)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/23 19:38
S118	22	S116 and (thin adj film adj transistor tft offt)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 19:40
S119	19	S116 and (thin adj film adj transistor tft offt) and (planar planari?e planari?ed planari?ation planari?)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 19:41
S120	537	(silicon-on-insulator "SOI") and driver and pixel and (planar planari?e planari?ed planari?ation planari? ing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 08:16
S121	0	(silicon-on-insulator "SOI") and driver and pixel and (planar planari?e planari?ed planari?ation planari? ing) and intergated adj circuit and (silicon semiconductor) near1 substrate and @ack<"20021225"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 08:17
S122	184	(silicon-on-insulator "SOI") and driver and pixel and (planar planari?e planari?ed planari?ation planari? ing) and integrated adj circuit and (silicon semiconductor) near1 substrate and @ack<"20021225"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 08:18
S123	139	(silicon-on-insulator "SOI") and driver and pixel and (planar planari?e planari?ed planari?ation planari? ing) and integrated adj circuit and (silicon semiconductor) near1 substrate and @ack<"20021225"	USPAT; EPO; JPO; IBM_TDB	OR	ON	2006/02/24 08:26

S124	1	(US-20040135157-\$).did.	US-PGPUB	OR	OFF	2006/02/24 08:41
S125	1	S124 and raised adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/24 09:40
S126	0	zhang.in. and stacked near4 tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/24 09:41
S127	0	semiconductor adj energy.in. and stacked near4 tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/24 09:41
S128	0	semiconductor adj energy.in. and stack\$3 near4 tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 09:42
S129	0	semiconductor adj energy.in. and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 09:42
S130	5688	semiconductor adj energy.as. and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 09:42

S131	21	semiconductor adj energy.as. and tft near4 stack\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 09:44
S132	457	tft near4 stack\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 09:44
S133	64	tft near4 stack\$4.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 10:38
S134	28	tft near4 stack\$4.ti,ab,clm. and (silicon semiconductor) near4 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 10:38
S135	1	(US-20040135157-\$).did.	US-PGPUB	OR	OFF	2006/02/24 15:03
S136	9	optical adj print adj head and (tft active adj matrix adj display)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:07
S137	7	optical adj print adj head and (active adj matrix)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:09

S138	5	optical adj print adj head and (active adj matrix) and print adj head and tft	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:09
S139	0	optical adj print adj head and (active adj matrix) and print adj head near20 tft	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:09
S140	0	optical adj print adj head and (active adj matrix) and print adj head same tft	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:09
S141	7	optical adj print adj head and (active adj matrix) and print adj head	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:12
S142	48	print adj head and ((active adj matrix) near20 tft) and print adj head	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:13
S143	1	print adj head and ((active adj matrix) near20 tft) near20 (print adj head)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:14

S144	1	print\$3 adj head and ((active adj matrix) near20 tft) near20 (print\$3 adj head)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:16
S145	0	print\$3 adj head and ((matrix adj2 display) near20 tft) near20 (print\$3 adj head)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:16
S146	1	print\$3 adj head and ((matrix) near20 tft) near20 (print\$3 adj head)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:28
S147	0	09-045930\$-\$\$.did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:28
S148	0	"09045930"\$-\$\$.did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:28
S149	2	jp-09045930\$-\$\$.did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 19:43

S150	0	"6255705".pn. and print\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:41
S151	1	(US-20040135157-\$).did.	US-PGPUB	OR	OFF	2006/02/24 17:21
S152	1	S151 and common	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/24 17:21
S153	1	S151 and common	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 17:21
S154	61	(US-20030141504-\$ or US-20020163000-\$ or US-20040135157-\$ or US-20030067043-\$ or US-20020168856-\$ or US-20040012053-\$ or US-20040007746-\$ or US-20040130015-\$ or US-20040094770-\$ or US-20030102473-\$ or US-20040125197-\$ or US-20040166659-\$ or US-20030170934-\$ or US-20040089939-\$ or US-20050100279-\$ or US-20030133668-\$ or US-20040155302-\$ or US-20040155301-\$ or US-20050087817-\$ or US-20040016976-\$ or US-20020061040-\$).did. or (US-6828227-\$ or US-5492851-\$ or US-5031187-\$ or US-6692837-\$ or US-6476485-\$ or US-6307264-\$ or US-4902637-\$ or US-6876008-\$ or US-6773943-\$ or US-6692845-\$ or US-6472718-\$ or US-6403985-\$ or US-6339233-\$ or US-6114715-\$ or US-5955747-\$ or US-5866922-\$ or US-5663581-\$ or US-5115284-\$ or US-4984035-\$ or US-4956683-\$ or US-4335501-\$ or US-T979005-\$ or US-5055907-\$ or US-	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2006/02/24 17:24

		5789766-\$ or US-6410960-\$ or US-6903427-\$).did. or (US-6849877-\$ or US-6861715-\$ or US-6812488-\$ or US-6717222-\$ or US-6706546-\$ or US- 6690845-\$ or US-6684007-\$ or US-6611635-\$ or US-6222755-\$ or US-5696714-\$ or US-6380572-\$). did. or (JP-10063807-\$ or JP-61102767-\$).did. or (JP-10063807-\$).did.				
S155	1	S154 and common near2 (source drain gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/24 17:25
S156	1	S154 and gate adj line	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/24 18:04
S157	40	tft and active adj matrix and compound adj semiconductor near10 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/24 18:05
S158	18	tft and active adj matrix and compound adj semiconductor near1 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/24 18:15
S159	0	tft and active adj matrix and compound adj semiconductor near1 channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 18:16

S160	0	tft and active adj matrix and (gan gaas compound adj semiconductor) near1 channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 18:16
S161	14	tft and (gan gaas compound adj semiconductor) near5 channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 18:17
S162	2	("20030067043").PNL	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/24 19:43
S163	7	"734294".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/25 13:52
S164	2	("5838608").PNL	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/25 14:34
S165	19	"5492851"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/25 14:34
S166	2	("5492851").PNL	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/25 14:41

S167	0	("743294.ap.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/25 14:41
S168	6	"743294".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/25 14:41
S169	7	"734294".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/25 14:42
S170	2	"20040175887".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/25 15:28
S171	2	("20030067043").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/25 16:03
S172	8789	((257/79) or (257/93) or (257/88) or (257/99) or (257/499) or (257/501) or (257/678) or (257/687) or (257/905) or (257/906) or (257/911)).CCL.S.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/25 16:04
S173	0	S172 and planarized adj (layer region film).clm. and (integrated adj circuit IC).clm. and (semiconductor silicon gan gaas sige) near2 substrate.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/25 16:06

S174	0	S172 and planarized near4 (layer region film).clm. and (integrated adj circuit IC).clm. and (semiconductor silicon gan gaas sige) near2 substrate.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/25 16:06
S175	1	S172 and planarized near4 (layer region film).ti.ab, clm. and (integrated adj circuit IC).ti.ab,clm. and (semiconductor silicon gan gaas sige) near2 substrate.ti.ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/25 16:06
S176	2	("6255705").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/08 20:03
S177	5	"384014".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/08 20:06
S178	2	("20040173808").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/08 20:06
S179	8	"561564"	DERWENT	OR	OFF	2006/12/08 20:07
S180	2	("20030067043").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/09 00:10
S181	1	(US-20040135157-\$).did.	US-PGPUB	OR	OFF	2007/05/26 00:19

S182	1	(US-20040135157-\$).did. and rough\$4	US-PGPUB	OR	ON	2007/05/26 00:20
S183	2	("6255705").PNL	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/26 00:21
S184	1	(US-20040135157-\$).did.	US-PGPUB	OR	OFF	2007/05/26 16:00
S186	1	(US-20040135157-\$).did.	US-PGPUB	OR	OFF	2007/05/26 16:01
S187	1	S186 and rough\$3	US-PGPUB	OR	OFF	2007/05/26 16:32
S188	1	S186 and rough\$3 and thin adj2 film	US-PGPUB	OR	OFF	2007/05/26 16:49
S189	1	S186 and compound	US-PGPUB	OR	OFF	2007/05/26 16:49
S190	1	S186 and epitaxial\$2 and thin and compound	US-PGPUB	OR	OFF	2007/05/26 17:16
S191	66	(planari?ation planari?e planari?ed planari?ing).ti,ab, clm. and (integrated adj circuit IC adj chip).ti,ab, clm. and (light-emitting light adj emitting).ti,ab,clm.	US-PGPUB	OR	ON	2007/05/26 17:19
S192	22	(planari?ation planari?e planari?ed planari?ing).ti,ab, clm. and (integrated adj circuit IC adj chip).ti,ab, clm. and (light-emitting light adj emitting).ti,ab,clm. and "257"/\$7.ccls.	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 20:18
S193	22	(planari?ation planari?e planari?ed planari?ing).ti,ab, clm. and (integrated adj circuit IC adj chip).ti,ab, clm. and (light-emitting light adj emitting).ti,ab,clm. and "257"/\$7.ccls.	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 20:26

S194	22	S193 and (planari?ation planari?e planari?ed planari?ing) and (integrated adj circuit IC adj chip) and (light-emitting light adj emitting) and "257"/\$7.ccls.	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 20:24
S195	1	S193 and (planari?ation planari?e planari?ed planari?ing) and (integrated adj circuit IC adj chip) and (light-emitting light adj emitting) and "257"/\$7.ccls. and monitoring adj device	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 20:25
S196	43	(planari?ation planari?e planari?ed planari?ing).ti,ab, cfm. and (integrated adj circuit IC adj chip).ti,ab, cfm. and (light-emitting light adj emitting) and "257"/\$7.ccls.	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 20:36
S197	4	(planari?ation planari?e planari?ed planari?ing).ti,ab, cfm. and (integrated adj circuit IC adj chip).ti,ab, cfm. and (light-emitting light adj emitting) and (257/79.ccls. 257/8\$1.ccls. 257/9\$1.ccls. 257/100.ccls. 257/101.ccls. 257/102.ccls. 257/103.ccls.)	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 20:37
S198	13	(planari?ation planari?e planari?ed planari?ing).ti,ab, cfm. and (integrated adj circuit IC adj chip).ti,ab, cfm. and (light-emitting light adj emitting laser) and (257/79.ccls. 257/8\$1.ccls. 257/9\$1.ccls. 257/100.ccls. 257/101.ccls. 257/102.ccls. 257/103.ccls. "372"/\$7.ccls.)	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 20:41
S199	72	(planari?ation planari?e planari?ed planari?ing).ti,ab, cfm. and (integrated adj circuit IC adj chip).ti,ab, cfm. and (light-emitting light adj emitting laser) and (thin adj film adj transistor 257/79.ccls. 257/8\$1.ccls. 257/9\$1.ccls. 257/100.ccls. 257/101.ccls. 257/102.ccls. 257/103.ccls. "372"/\$7.ccls.)	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 20:42

S200	38	(planari?ation planari?e planari?ed planari?ing).ti,ab, ctm. and (integrated adj circuit IC adj chip).ti,ab, ctm. and (light-emitting light adj emitting laser) and (thin adj film adj transistor 257/79.ccls. 257/8\$1.ccls. 257/9\$1.ccls. 257/100.ccls. 257/101.ccls. 257/102.ccls. 257/103.ccls. "372"/\$7.ccls.) and @ad<"20031225"	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 20:48
S201	38	(planari?ation planari?e planari?ed planari?ing).ti,ab, ctm. and (integrated adj circuit IC adj chip).ti,ab, ctm. and (light-emitting light adj emitting laser) and (thin adj film adj transistor 257/79.ccls. 257/8\$1.ccls. 257/9\$1.ccls. 257/100.ccls. 257/101.ccls. 257/102.ccls. 257/103.ccls. "372"/\$7.ccls.) and @ad<"20031225" and (planari?ation planari?e planari?ed planari?ing)	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 20:57
S202	2	("6734930").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/26 20:57
S203	1	"5504599".PN.	USPAT; USOCR	OR	OFF	2007/05/26 20:58
S204	1	"5796509".PN.	USPAT; USOCR	OR	OFF	2007/05/26 20:59
S205	1	"5926239".PN.	USPAT; USOCR	OR	OFF	2007/05/26 21:01
S206	1	"6194837".PN.	USPAT; USOCR	OR	OFF	2007/05/26 21:01
S207	1	"6441551".PN.	USPAT; USOCR	OR	OFF	2007/05/26 21:02
S208	1	"6441551".PN.	USPAT; USOCR	OR	OFF	2007/05/26 21:03
S209	1	"6556260".PN.	USPAT; USOCR	OR	OFF	2007/05/26 21:03

S210	1	"6628068".PN.	USPAT; USOCR	OR	OFF	2007/05/26 21:04
S211	1	"20020196387".PN.	US-PGPUB	OR	OFF	2007/05/26 21:04
S212	1	"20030063231".PN.	US-PGPUB	OR	OFF	2007/05/26 21:05
S213	1	"20030127656".PN.	US-PGPUB	OR	OFF	2007/05/26 21:22
S214	2	("5796509").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/26 21:23
S215	0	S214 and (planarized planarised planarize planarise planarization planarisation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/26 21:24
S216	2125	(planarized planarised planarize planarise planarization planarisation) and lod and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 21:24
S217	738	(planarized planarised planarize planarise planarization planarisation) and (liquid adj crystal adj display lod) and (thin adj film adj transistor tft) and (planarized planarised planarize planarise planarization planarisation).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 21:26
S218	464	(planarized planarised planarize planarise planarization planarisation) and (liquid adj crystal adj display lod) and (thin adj film adj transistor tft) and (planarized planarised planarize planarise planarization planarisation).ti,ab,clm. and @ad<"20031231"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 21:27

S219	53	(planarized planarised planarize planarise planarization planarisation) and ((el electroluminescent) adj (layer film)) and (thin adj film adj transistor tft) and (planarized planarised planarize planarise planarization planarisation).ti,ab,clm. and @ad<"20031231"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 22:45
S220	717	(planarized planarised planarize planarise planarization planarisation) and ((el electroluminescent) adj (layer film)) and (thin adj film adj transistor tft) and (planarized planarised planarize planarise planarization planarisation)".ti,ab" and (planarized planarised planarize planarise planarization planarisation).clm. and @ad<"20031231"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 21:35
S221	4	(planarized planarised planarize planarise planarization planarisation) and ((el electroluminescent) adj (layer film)) and (thin adj film adj transistor tft) and (planarized planarised planarize planarise planarization planarisation).ti,ab. and (planarized planarised planarize planarise planarization planarisation).clm. and @ad<"20031231"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 21:35
S222	51	ppv near3 semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 22:47
S223	70	(polyparaphenylene adj vinylene polyvinyl adj carbazole polyfluorane) near6 semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 22:49
S224	55	(polyparaphenylene adj vinylene polyvinyl adj carbazole polyfluorane) near6 semiconductor	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 22:54

S225	0	(polyparaphenylene adj vinylene and polyvinyl adj carbazole and polyfluorane) near6 semiconductor	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 22:53
S226	6	(polyparaphenylene adj vinylene polyvinyl adj carbazole polyfluorane) near6 semiconductor and electroluminescent	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 23:24
S227	6	(polyparaphenylene adj vinylene polyvinyl adj carbazole polyfluorane) near6 (organic adj compound) and electroluminescent	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 00:30
S228	4021	(planari?ation planari?e planari?ed planri?ing) near4 (semiconductor silicon)	US-PGPUB	OR	ON	2007/05/27 10:08
S229	12258	(planari?ation planari?e planari?ed planri?ing) near4 (semiconductor silicon)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 10:08
S230	4511	(planari?ation planari?e planari?ed planari?ing) near1 (semiconductor silicon)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 10:09
S231	0	(planari?ation planari?e planari?ed planari?ing) near1 (semiconductor silicon) and tft and el adj (layer film)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 10:09

S232	7	(planari?ation planari?e planari?ed planari?ing) near2 (semiconductor silicon) and tft and el adj (layer film)	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 10:10
S233	26	(planari?ation planari?e planari?ed planari?ing) near3 (semiconductor silicon) and tft and el adj (layer film)	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 10:14
S234	446	(planari?ation planari?e planari?ed planari?ing) near3 (semiconductor silicon) and tft	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 10:14
S235	314	(planari?ation planari?e planari?ed planari?ing) near2 (semiconductor silicon) and tft	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 10:35
S236	18	(planari?ation planari?e planari?ed planari?ing) near2 (semiconductor silicon) and (257/79.cds. 257/8\$1.cds. 257/9\$1.cds. 257/10\$1.cds.) and @ad<"20031231"	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 10:54
S237	0	"20010019133".pn. and common adj electrode	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 10:55

S238	2	"20010019133".pn. and electrode	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 11:15
S239	0	(semiconductor near1 energy).as. and optical adj print adj head.clm. and (EL adj (layer film))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 11:16
S240	0	optical adj print adj head.clm. and (EL adj (layer film))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 11:16
S241	2	optical adj print adj head.ti,ab,clm. and (EL adj (layer film))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 11:19
S242	2	jp-2001167874\$-\$\$.did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 11:36
S243	2	("6841183").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/27 11:37

S244	2	("6841813").PNL	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/27 11:47
S245	18433	((257/79) or (257/8\$1) or (257/9\$1) or (257/100) or (257/101) or (257/102) or (257/103) or (257/499) or (257/501) or (257/678) or (257/905) or (257/906) or (257/911)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/27 11:52
S246	18676	((257/79) or (257/8\$1) or (257/9\$1) or (257/100) or (257/101) or (257/102) or (257/103) or (257/499) or (257/501) or (257/678) or (257/905) or (257/906) or (257/911) or (257/e31.095) or (257/e31.096)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/27 11:52
S247	37	S246 and (planari?e planari?ed planari?ing planari?ation) near20 (semiconductor silicon).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 12:01
S248	7	(fujiwara.in. sakuta.in. abiko.in. oki adj data.as. ogihara.in.) and (planari?e planari?ed planari?ing planari?ation) near20 (semiconductor silicon).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 12:11
S249	4	(fujiwara.in. sakuta.in. abiko.in. oki adj data.as. ogihara.in.) and (planari?e planari?ed planari?ing planari?ation) near20 (semiconductor silicon).clm. and compound adj semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 12:41
S250	67	nakamura.in. and blue adj "LED"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 12:42

S251	9	nakamura.in. and blue adj "LED" and compound adj semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 12:43
S252	164	nakamura.in. and GaN and compound adj semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 12:45
S253	4	nakamura.in. and GaN and compound adj semiconductor and (planari?ing planari?e planari?ation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 12:46
S254	293	GaN and compound adj semiconductor and (planari?ing planari?e planari?ation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 12:53
S255	4	"651586".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 12:54
S256	4	"651586".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 12:54
S257	1	(US-20040135157-\$).did.	US-PGPUB	OR	ON	2008/01/09 08:33
S258	1	(US-20040135157-\$).did. and (flat flatness plaraized planarization nanometer nm)	US-PGPUB	OR	ON	2008/01/09 08:37

S259	2	("20010019133").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/09 08:43
S260	2	jp-2001167874\$-\$.did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/09 08:42
S261	1	S259 and (planari?ed planari?ing planari?e planari?ation)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/09 11:42
S262	0	("298736.ap.").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/09 11:42
S263	9	"298736".ap.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/09 11:49
S264	5	"3632470".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/09 11:49

S265	2	("7253716").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/09 11:50
S266	0	("(planarizeplanarizationplanarizing).ti,ab,clm. andflatnessnear20(nmangstrom)").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/10 11:46
S267	62	(planarize planarization planarizing).ti,ab,clm. and flatness near20 (nm angstrom)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/10 11:46
S268	1	(US-20040135157-\$).did.	US-PGPUB	OR	ON	2008/01/10 11:48
S269	1	(US-20040135157-\$).did. and interdielectric near10 (thick thickness)	US-PGPUB	OR	ON	2008/01/10 11:54
S270	8	mondtxp.	USPAT	OR	ON	2008/01/10 13:57
S271	4604	pixel adj electrode and (electroluminescen\$2 EL) adj (element device)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/10 13:58

S272	271	pixel adj electrode and (electroluminescen\$2 EL) adj (element device) and planari?e	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/10 13:58
S273	144	flatness near10 (peak-to-valley root-mean-square rms) and (silicon semiconductor) and substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/10 16:23
S274	1	(US-20040135157-\$.did.	US-PGPUB	OR	ON	2008/01/10 16:34
S275	1	(US-20040135157-\$.did. and flatness	US-PGPUB	OR	ON	2008/01/10 16:35
S276	9	(US-20050087510-\$. or US-20050051437-\$. or US- 20050009296-\$. or US-20040132253-\$. or US- 20040130775-\$. or US-20040113150-\$. or US- 20030038321-\$. or US-20030006406-\$. or US- 20020195440-\$.did.	US-PGPUB	OR	ON	2008/01/10 16:55
S277	1	(US-20040135157-\$.did.	US-PGPUB	OR	ON	2008/01/10 17:00
S278	0	(US-20040135157-\$.did. and "entire"	US-PGPUB	OR	ON	2008/01/10 17:00
S279	0	(US-20040135157-\$.did. and ("complete" "entire")	US-PGPUB	OR	ON	2008/01/10 17:01
S280	0	(US-20040135157-\$.did. and (complete entire)	US-PGPUB	OR	ON	2008/01/10 17:01
S281	1	(US-20040135157-\$.did. and (complete entire full)	US-PGPUB	OR	ON	2008/01/10 17:01
S282	1	(US-20040135157-\$.did. and "same" near2 (thick thickness)	US-PGPUB	OR	OFF	2008/01/11 10:38

S283	12941	((257/79) or (257/88) or (257/93) or (257/98) or (257/99) or (257/499) or (257/501) or (257/678) or (257/905) or (257/906) or (257/911)).CCL.S.	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/11 11:36
S284	2	S283 and (planarized planarization Planarizing planarize) and flatness near 20 (thick thickness angstrom nm) and (VLSI ULSI integrated adj circuit IC)	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/11 11:39
S285	2	("20020187650").PN.	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/11 14:39
S286	2	("20010019133").PN.	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/11 14:57
S287	1	(US-20040135157-\$).did.	US-PGPUB	OR	ON	2008/08/30 16:01
S288	0	("1aninorganic").PN.	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/08/30 16:01

S289	0	S287 and inorganic	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/30 16:01
S290	2	("20010019133").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/08/30 16:09
S291	718	transparent near4 metal near4 pixel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/30 16:10
S292	0	transparent near4 metal near4 pixel adj electrode and electroluminescen\$2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/30 16:11
S293	19	transparent near4 metal near4 pixel adj electrode and electroluminescen\$2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/30 16:11
S294	8	transparent near4 metal near4 pixel adj electrode and electroluminescen\$2 and @ad< "20021225"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/30 16:14

S295	1	S287 and (metal metallic)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/30 16:17
S296	9469	(metal metallic) near4 ((ito indium-tin-oxide zto zinc-tin-oxide)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/30 16:20
S297	2336	(metal metallic) near1 ((ito indium-tin-oxide zto zinc-tin-oxide)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/30 16:20
S298	1246	(metal metallic) near1 ((ito indium-tin-oxide zto zinc-tin-oxide) and pixel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/30 16:20
S299	188	(metal metallic) near1 ((ito indium-tin-oxide zto zinc-tin-oxide) same pixel and @ad<"20021224"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/30 16:20
S300	84	(metal metallic) near1 ((ito indium-tin-oxide zto zinc-tin-oxide) near6 pixel and @ad<"20021224"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/30 16:21

S301	94	organic adj semiconductor adj compound and @ad<"20021224"	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/30 19:43
S302	12	organic adj semiconductor adj compound.ti. and @ad<"20021224"	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/30 19:43
S303	14	organic adj semiconductor adj compound.ti,ab,clm. and transistor and @ad<"20021224"	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/30 19:44
S304	184	(planari?ation planari?e\$1 planari?ing) and transistor and (peak-to-valley roughness flatness atomically adj flat) near4 ("10" adj nm "5" adj nm "1" adj nm)	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/30 19:51
S305	36	(planari?ation planari?e\$1 planari?ing) and transistor and (peak-to-valley roughness flatness atomically adj flat) near4 ("10" adj nm "5" adj nm "1" adj nm) and @ad<"20021224"	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/30 19:52
S306	9	(planari?ation planari?e\$1 planari?ing).ti,ab,clm. and transistor and (peak-to-valley roughness flatness atomically adj flat) near4 ("10" adj nm "5" adj nm "1" adj nm) and @ad<"20021224"	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/30 19:55

S307	0	(planari?ation planari?e\$1 planari?ing).ti,ab,dlm. and transistor and (peak-to-valley roughness flatness atomically adj flat) near4 ("10" adj nm "5" adj nm "1" adj nm) and @ad<"20021224" and (light-emitting ligh adj emitting)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/30 20:04
S308	1	(planari?ation planari?e\$1 planari?ing).ti,ab,dlm. and transistor and (peak-to-valley roughness flatness atomically adj flat) near4 ("10" adj nm "5" adj nm "1" adj nm) and @ad<"20021224" and (light-emitting light adj emitting)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/30 20:04
S309	1	(planari?ation planari?e\$1 planari?ing).ti,ab,dlm. and transistor and (peak-to-valley roughness flatness atomically adj flat) near4 ("10" adj nm "5" adj nm "1" adj nm) and @ad<"20021224" and (light-emitting light adj emitting) and oxide adj cap	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/30 20:25
S310	1	(US-20040135157-\$.)did.	US-PGPUB	OR	ON	2008/08/30 20:41
S311	1	(US-20040135157-\$.)did. and edge	US-PGPUB	OR	ON	2008/08/30 20:42
S312	0	"6242324".pn. and (planarize planarizing planarization)	US-PGPUB	OR	OFF	2008/08/31 09:13
S313	0	"6242324".pn. and (planarize planarizing planarization)	US-PGPUB	OR	ON	2008/08/31 09:13
S314	0	"6242324".pn.	US-PGPUB	OR	ON	2008/08/31 09:13
S315	2	("6242324").PNL	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/08/31 09:14

S316	1	S315 and (planarize planarized planarization planarizing)	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/31 09:14
S317	498	odte near3 semiconductor and detector	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/31 10:29
S318	161	odte near3 semiconductor near6 detector	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/31 10:30
S319	0	omos and intergated and (light adj emitting light \$1emitting) adj (device element diode) and common adj electrode	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/31 10:46
S320	201	omos and integrated and (light adj emitting light \$1emitting) adj (device element diode) and common adj electrode	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/31 10:46
S321	91	omos and integrated and (light adj emitting light \$1emitting) adj (device element diode) and common adj electrode and @ad<"20021224"	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/31 10:47

S322	13	(257/8\$1.ccls. 257/9\$1.ccls. 257/10\$1.ccls.) and integrated adj circuit and cmos and common adj electrode	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/31 11:35
S323	1	(257/8\$1.ccls. 257/9\$1.ccls. 257/10\$1.ccls.) and integrated adj circuit and cmos and common adj electrode and print	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/31 12:07
S324	18	(257/8\$1.ccls. 257/9\$1.ccls. 257/10\$1.ccls.) and integrated adj circuit and common adj electrode and print	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/31 12:07
S325	2696841	(257/8\$1.ccls. 257/9\$1.ccls. 257/10\$1.ccls.) and integrated adj circuit and common adj electrode and print adh head	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/31 12:08
S326	12	(257/8\$1.ccls. 257/9\$1.ccls. 257/10\$1.ccls.) and integrated adj circuit and common adj electrode and print adj head	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/31 12:08
S327	3	"743104".ap.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/31 12:40

S328	1	(US-20040135157-\$.)\$.did.	US-PGPUB	OR	ON	2008/08/31 12:41
S329	1	(US-20040135157-\$.)\$.did.	US-PGPUB	OR	ON	2008/08/31 12:41
S330	1	S329 and (planari?e\$1 planari?ing)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/31 12:42
S331	1557	(planari?e\$1 planari?ing) near3 (region layer) near20 (depositing deposit forming) near20 metal	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/31 13:15
S332	0	(planari?e\$1 planari?ing) near3 (region layer) near20 (depositing deposit forming) near20 metal and interdielectric near4 (planarizing planarize planarization)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/31 13:16
S333	8	(planari?e\$1 planari?ing) near3 (region layer) near20 (depositing deposit forming) near20 metal and interdielectric	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/31 13:16
S334	5704	(planari?e\$1 planari?ing) near3 method.ti,ab,clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/31 13:25

S335	0	(planari?e\$1 planari?ing) near3 method.ti,ab,clm. and planari?ing near4 dielectric and planari?ing near4 metal	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/31 13:26
S336	125	(planari?e\$1 planari?ing) near3 method.ti,ab,clm. and planari?ing near4 dielectric and planari?ing near4 metal	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/31 13:26
S337	35	(planari?e\$1 planari?ing) near3 method.ti,ab,clm. and planari?ing near4 dielectric and planari?ing near4 metal and barrier and @ad<"20021224"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/31 13:39
S338	86	barrier adj (layer film) and cmos and plurality near2 (light\$1emitting light adj emitting)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/31 13:48
S339	2	metal adj barrier adj (layer film) and plurality near2 (light\$1emitting light adj emitting)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/31 13:50
S340	13	barrier adj (layer film) near10 (common adj electrode) and (light\$1emitting light adj emitting)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/31 13:52

S341	2812	257/79	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/31 15:44
S342	13821	((257/79) or (257/88) or (257/93) or (257/98) or (257/99) or (257/499) or (257/501) or (257/678) or (257/905) or (257/906) or (257/911)).OCLS	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/08/31 15:46
S343	1267	S342 and (combined adj2 apparatus integrated adj circuit IC) and (silicon si) near2 substrate and (planari?e\$1 planari?ing planari?ation) and thin adj film and metal adj (layer film) and light\$1emitting and inorganic near3 compound and edge\$1 near3 (extend extending)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/31 15:49
S344	0	S342 and (combined adj2 apparatus integrated adj circuit IC) and (silicon si) near2 substrate and (planari?e\$1 planari?ing planari?ation) and thin adj film and metal adj (layer film) and light\$1emitting and inorganic near3 compound and edge\$1 near3 (extend extending)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/31 15:50
S345	0	((ogihara).in. (fujiwara).in. (sakuta).in. (abiko).in. (oki).as. and (combined adj2 apparatus integrated adj circuit IC) and (silicon si) near2 substrate and (planari?e\$1 planari?ing planari?ation) and thin adj film and metal adj (layer film) and light\$1emitting and inorganic near3 compound and edge\$1 near3 (extend extending)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/31 15:51

S346	2	"6242324".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/19 10:21
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